

IN THE SPECIFICATION:

Please replace paragraph [0039] with the following.

[0039] Alternatively, the interconnect may be formed from a mixed phase layer, such as the TiN/TiSi_x layer formed by the method disclosed in United States Patent ~~5,525,518~~ 5,252,518 (the "518 patent), issued to Gurtej S. Sandhu et al. on October 12, 1993, the disclosure of which is hereby incorporated by reference in its entirety. The process of the '518 patent includes reacting Ti(NR₂)₄, where the titanium atom is bonded to the nitrogen atom which is in turn bonded to two hydrogen atoms or a carbon-containing radical (R), with an organic silane reactive gas, such as tris(dimethylamino) silane (SIN).